

## 2N6342-2N6349

## SILICON BIDIRECTIONAL TRIODE THYRISTORS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating   | Symbol              | Value                    | Unit                 |
|--|---------------------|--------------------------|----------------------|
| <b>Peak repetitive off-state voltage<sup>(1)</sup></b><br>(Gate open, $T_J = -40$ to $110^\circ\text{C}$ , $\frac{1}{2}$ sine wave 50 to 60Hz)<br>2N6342, 2N6346<br>2N6343, 2N6347<br>2N6344, 2N6348<br>2N6345, 2N6349 | $V_{\text{DRM}}$    | 200<br>400<br>600<br>800 | Volts                |
| <b>RMS on-state current</b><br>Full cycle sine wave 50 to 60Hz<br>$T_C = 80^\circ\text{C}$<br>$T_C = 90^\circ\text{C}$   | $I_{\text{T(RMS)}}$ | 8<br>4                   | Amps                 |
| <b>Peak non-repetitive surge current</b><br>(One full cycle, 60Hz, $T_C = 80^\circ\text{C}$ )<br>Preceded and followed by rated current  | $I_{\text{TSM}}$    | 100                      | Amps                 |
| <b>Circuit fusing</b> ( $t = 8.3\text{ms}$ )   | $I^2t$              | 40                       | $\text{A}^2\text{s}$ |
| <b>Peak gate power</b><br>( $T_C = 80^\circ\text{C}$ , pulse width = $2\mu\text{s}$ )  | $P_{\text{GM}}$     | 20                       | Watts                |
| <b>Average gate power</b><br>( $T_C = 80^\circ\text{C}$ , $t = 8.3\text{ms}$ )   | $P_{\text{G(AV)}}$  | 0.5                      | Watts                |
| <b>Peak gate current</b>   | $I_{\text{GM}}$     | 2                        | Amps                 |
| <b>Peak gate voltage</b>   | $V_{\text{GM}}$     | 10                       | Volts                |
| <b>Operating temperature range</b>   | $T_J$               | -40 to 125               | $^\circ\text{C}$     |
| <b>Storage temperature range</b>   | $T_{\text{stg}}$    | -40 to 150               | $^\circ\text{C}$     |

Note 1:  $V_{\text{DRM}}$  for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

### THERMAL CHARACTERISTICS

| Characteristic                              | Symbol                | Max | Unit               |
|---|-----------------------|-----|--------------------|
| <b>Thermal resistance, junction to case</b> | $R_{\theta\text{JC}}$ | 2.2 | $^\circ\text{C/W}$ |

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage, unless otherwise noted)

| Characteristic   | Symbol           | Min                        | Typ                       | Max                                | Unit                |
|--|------------------|----------------------------|---------------------------|------------------------------------|---------------------|
| <b>Peak blocking current</b><br>( $V_D = \text{rated } V_{\text{DRM}}$ , gate open)<br>$T_J = 25^\circ\text{C}$<br>$T_J = 100^\circ\text{C}$   | $I_{\text{DRM}}$ | -<br>-                     | -<br>-                    | 10<br>2                            | $\mu\text{A}$<br>mA |
| <b>Peak on-state voltage</b><br>( $I_{\text{TM}} = 11\text{A}$ peak, pulse width = 1 to 2ms, duty cycle $\leq 2\%$ )   | $V_{\text{TM}}$  | -                          | 1.3                       | 1.55                               | Volts               |
| <b>Gate trigger current (continuous dc)</b><br>( $V_D = 12\text{Vdc}$ , $R_L = 100\text{ohms}$ )<br>(Minimum gate pulse width = $2\mu\text{s}$ )<br>MT2+, G+ All types<br>MT2+, G- 2N6346-2N6349<br>MT2-, G- All types<br>MT2-, G+ 2N6346-2N6349<br>MT2+, G+:MT2-, G-, $T_C = -40^\circ\text{C}$ All types<br>MT2+, G-:MT2-, G+, $T_C = -40^\circ\text{C}$ , 2N6346-2N6349 | $I_{\text{GT}}$  | -<br>-<br>-<br>-<br>-<br>- | 12<br>12<br>20<br>35<br>- | 50<br>75<br>50<br>75<br>100<br>125 | mA                  |

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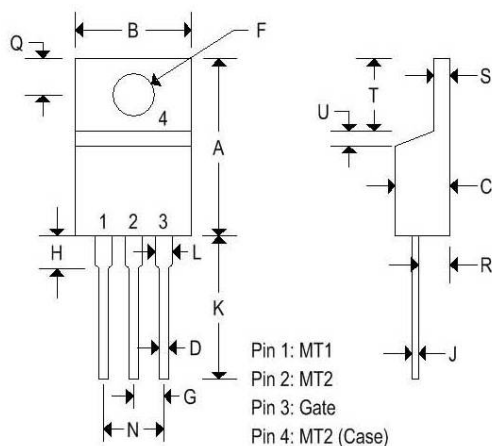
## SILICON BIDIRECTIONAL TRIODE THYRISTORS

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage, unless otherwise noted)

| Characteristic   | Symbol   | Min | Typ | Max | Unit                   |
|--|----------|-----|-----|-----|------------------------|
| <b>Gate trigger voltage (continuous dc)</b><br>( $V_D = 12\text{Vdc}$ , $R_L = 100\text{ohms}$ )<br>(Minimum gate pulse width = $2\mu\text{s}$ )<br>MT2+, G+ All types<br>MT2+, G- 2N6346-2N6349<br>MT2-, G- All types<br>MT2-, G+ 2N6346-2N6349<br>MT2+, G+:MT2-, G-, $T_C = -40^\circ\text{C}$ All types<br>MT2+, G-:MT2-, G+, $T_C = -40^\circ\text{C}$ , 2N6346-2N6349<br>( $V_D = \text{rated } V_{DRM}$ , $R_L = 10\text{kohms}$ , $T_J = 100^\circ\text{C}$ )<br>MT2+, G+; MT2-, G- All types<br>MT2+, G-;MT2-, G-, 2N6346-2N6349 | $V_{GT}$ | -   | 0.9 | 2.0 | Volts                  |
| <b>Holding current</b><br>( $V_D = 12\text{Vdc}$ , gate open)<br>( $I_T = 200\text{mA}$ )  | $I_H$    | -   | 6   | 40  | mA                     |
| <b>Turn-on time</b><br>( $V_D = \text{rated } V_{DRM}$ , $I_{TM} = 11\text{A}$ , $I_{GT} = 120\text{mA}$ , rise time = $0.1\mu\text{s}$ , pulse width = $2\mu\text{s}$ )   | $t_{gt}$ | -   | 1.5 | 2   | $\mu\text{s}$          |
| <b>Critical rate of rise of commutation voltage</b><br>( $V_D = \text{rated } V_{DRM}$ , $I_{TM} = 11\text{A}$ , commutating $di/dt = 4.0\text{A/ms}$ , gate unenergized, $T_C = 80^\circ\text{C}$ )   | $dv/dt$  | -   | 5   | -   | $\text{V}/\mu\text{s}$ |

### MECHANICAL CHARACTERISTICS

|         |                             |
|---------|-----------------------------|
| Case    | TO-220AB                    |
| Marking | Body painted, alpha-numeric |
| Pin out | See below                   |

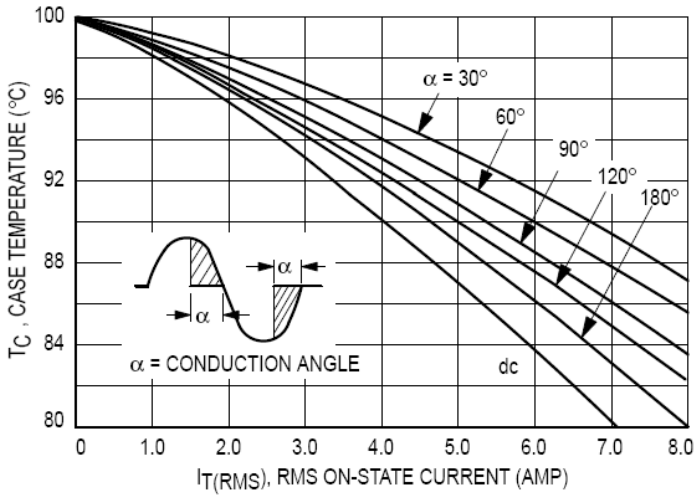


|   | TO-220AB |       |             |        |
|---|----------|-------|-------------|--------|
|   | Inches   |       | Millimeters |        |
|   | Min      | Max   | Min         | Max    |
| A | 0.575    | 0.620 | 14.600      | 15.750 |
| B | 0.380    | 0.405 | 9.650       | 10.290 |
| C | 0.160    | 0.190 | 4.060       | 4.820  |
| D | 0.025    | 0.035 | 0.640       | 0.890  |
| F | 0.142    | 0.147 | 3.610       | 3.730  |
| G | 0.095    | 0.105 | 2.410       | 2.670  |
| H | 0.110    | 0.155 | 2.790       | 3.930  |
| J | 0.014    | 0.022 | 0.360       | 0.560  |
| K | 0.500    | 0.562 | 12.700      | 14.270 |
| L | 0.045    | 0.055 | 1.140       | 1.390  |
| N | 0.190    | 0.210 | 4.830       | 5.330  |
| Q | 0.100    | 0.120 | 2.540       | 3.040  |
| R | 0.080    | 0.110 | 2.040       | 2.790  |
| S | 0.045    | 0.055 | 1.140       | 1.390  |
| T | 0.235    | 0.255 | 5.970       | 6.480  |
| U | -        | 0.050 | -           | 1.270  |
| V | 0.045    | -     | 1.140       | -      |
| Z | -        | 0.080 | -           | 2.030  |

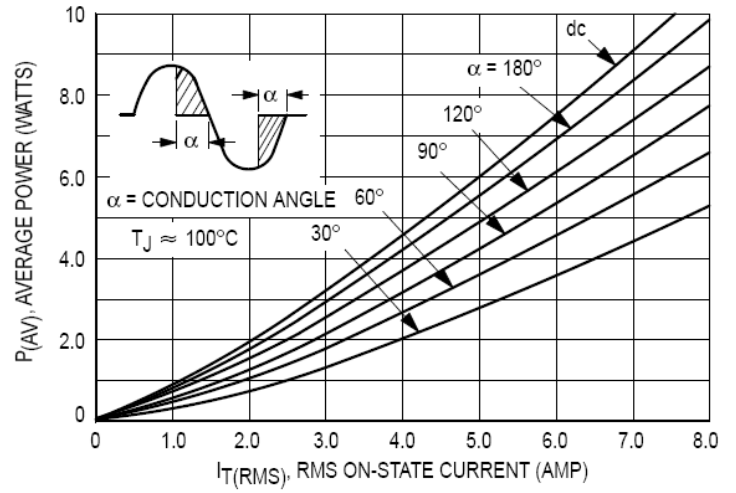
# DIGITRON SEMICONDUCTORS

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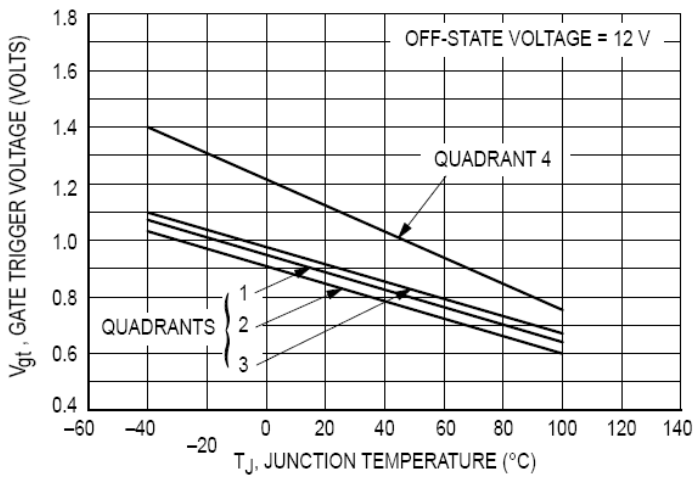
**FIGURE 1 – RMS CURRENT DERATING**



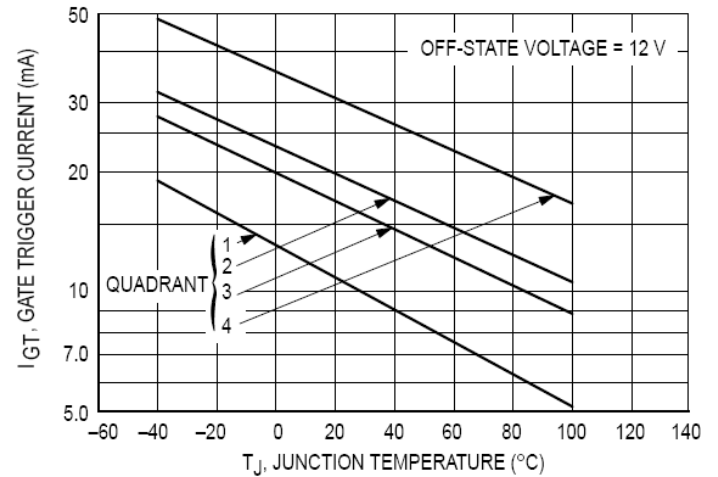
**FIGURE 2 – ON-STATE POWER DISSIPATION**



**FIGURE 3 – TYPICAL GATE TRIGGER VOLTAGE**



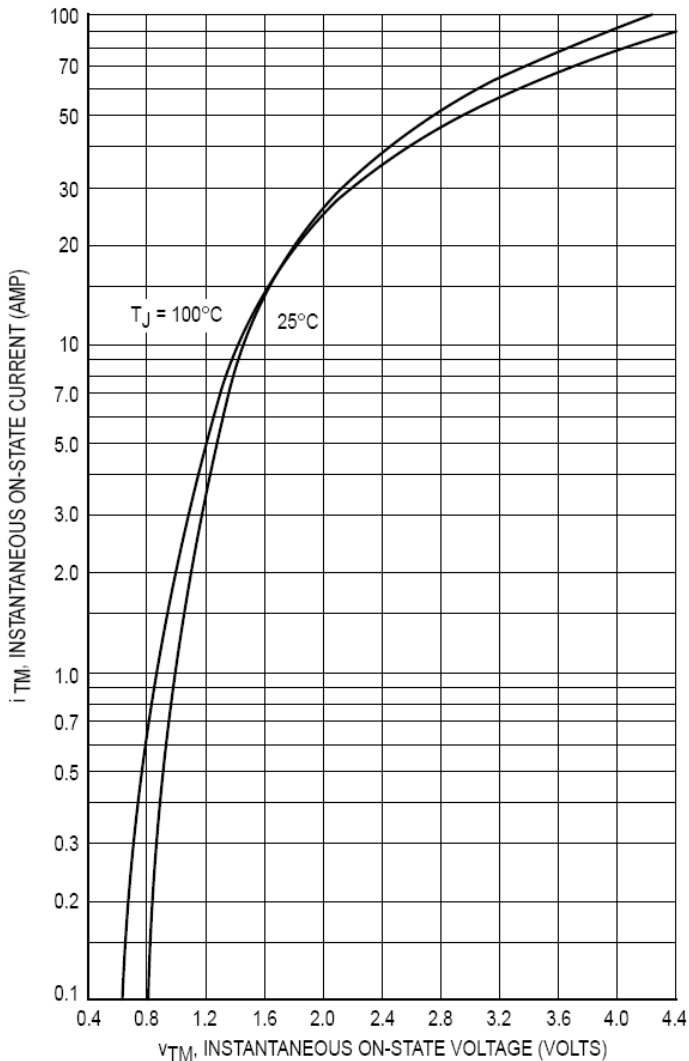
**FIGURE 4 – TYPICAL GATE TRIGGER CURRENT**



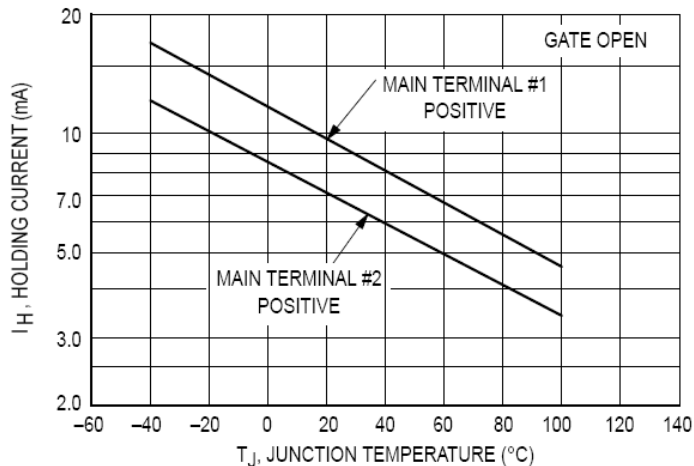
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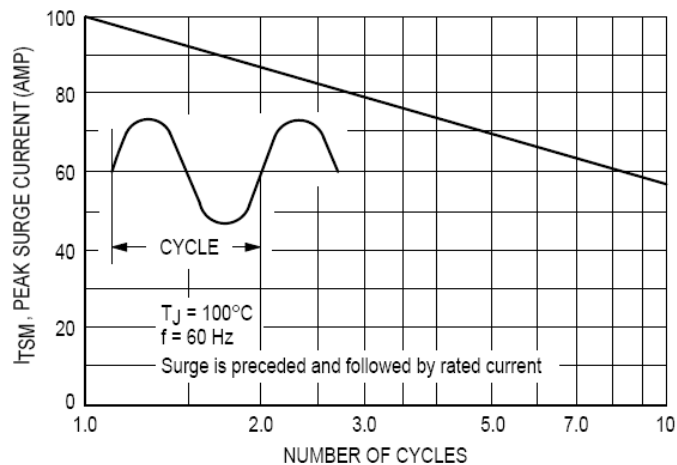
**FIGURE 5 – ON-STATE CHARACTERISTICS**



**FIGURE 6 – TYPICAL HOLDING CURRENT**



**FIGURE 7 – MAXIMUM NON-REPETITIVE SURGE CURRENT**



**FIGURE 8 – TYPICAL THERMAL RESPONSE**

